Product data sheet

1. General description

NPN low V_{CEsat} transistor in a SOT223 (SC-73) medium power Surface-Mounted Device (SMD) plastic package.

PNP complement: PBSS4021PZ

2. Features and benefits

- Very low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- High energy efficiency due to less heat generation
- · Smaller required Printed-Circuit Board (PCB) area than for conventional transistors
- AEC-Q101 qualified

3. Applications

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	20	V
I _C	collector current		-	-	8	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	20	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = 6 A; I_B = 600 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	14	20	mΩ



20 V, 8 A NPN low VCEsat transistor

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	4	С
2	С	collector		
3	E	emitter		B—[w]
4	С	collector	1 2 3	Ė
			SC-73 (SOT223)	sym123

6. Ordering information

Table 3. Ordering information

Type number Package					
	Name	Description	Version		
PBSS4021NZ		plastic, surface-mounted package with increased heatsink; 4 leads; 2.3 mm pitch; 6.5 mm x 3.5 mm x 1.65 mm body	SOT223		

7. Marking

Table 4. Marking codes

Type number	Marking code
PBSS4021NZ	PB4021
	NZ

20 V, 8 A NPN low VCEsat transistor

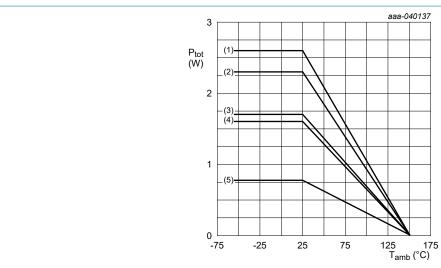
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	20	V
V _{CEO}	collector-emitter voltage	open base		-	20	V
V _{EBO}	emitter-base voltage	open collector		-	5	V
Ic	collector current			-	8	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	20	А
I _B	base current			-	1	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	0.77	W
			[2]	-	1.7	W
			[3]	-	1.6	W
			[4]	-	2.3	W
			[5]	-	2.6	W
T _j	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided, 35 µm copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided, 35 μm copper, tin-plated, mounting pad for collector 6 cm².
- [3] Device mounted on an FR4 PCB, 4-layer, tin-plated and standard footprint.
- [4] Device mounted on an FR4 PCB, 4-layer, tin-plated, mounting pad for collector 1 cm²
- [5] Device mounted on a ceramic PCB, Al₂O₃, single-sided, 35 µm copper, tin-plated and standard footprint.



- (1) Ceramic PCB, Al₂O₃, single-sided, 35 µm copper, standard footprint
- (2) FR4 PCB, 4-layer copper, 1 cm²
- (3) FR4 PCB, single-sided, 35 µm copper, 6 cm²
- (4) FR4 PCB, 4-layer copper, standard footprint
- (5) FR4 PCB, single-sided, 35 µm copper, standard footprint

Fig. 1. Power derating curves

PBSS4021NZ

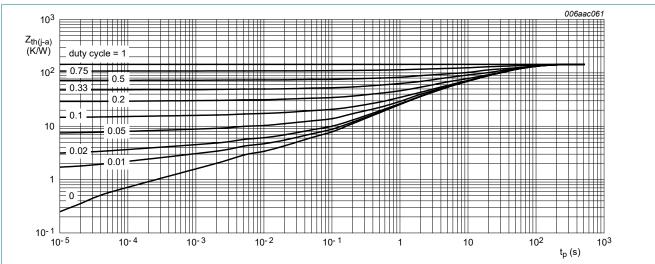
20 V, 8 A NPN low VCEsat transistor

9. Thermal characteristics

Table 6. Thermal characteristics

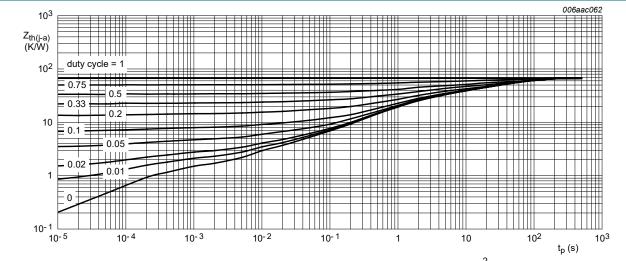
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
ui(j-a)		esistance from in free air [1] [2] [3] [4]	[1]	-	-	160	K/W
	junction to ambient		[2]	-	-	75	K/W
			[3]	-	-	80	K/W
			[4]	-	-	55	K/W
			[5]	-	-	50	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	11	K/W

- [1] Device mounted on an FR4 PCB, single-sided, 35 µm copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided, 35 μm copper, tin-plated, mounting pad for collector 6 cm².
- [3] Device mounted on an FR4 PCB, 4-layer, tin-plated and standard footprint.
- [4] Device mounted on an FR4 PCB, 4-layer, tin-plated, mounting pad for collector 1 cm².
- [5] Device mounted on a ceramic PCB, Al₂O₃, single-sided, 35 μm copper, tin-plated and standard footprint.



FR4 PCB, single-sided, 35 µm copper, tin-plated and standard footprint

Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

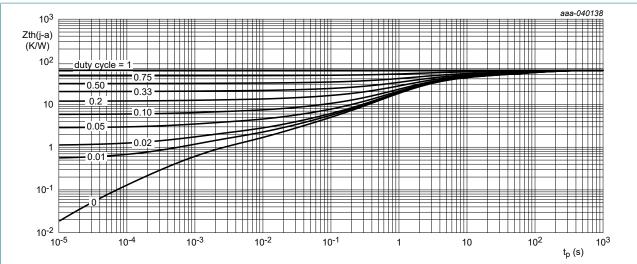


FR4 PCB, single-sided, 35 µm copper, tin-plated, mounting pad for collector 6 cm²

Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

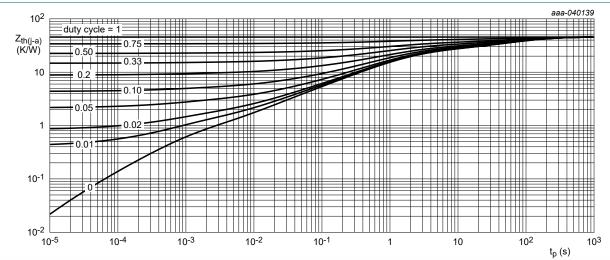
PBSS4021NZ

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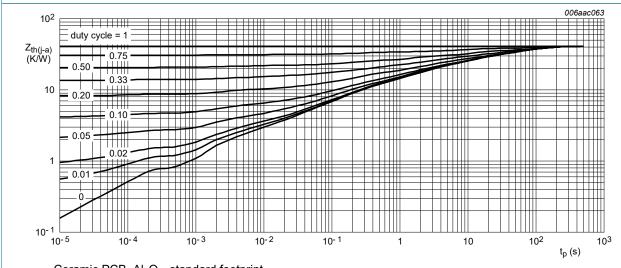
FR4 PCB, 4-layer, tin-plated and standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, 4-layer, tin-plated mounting pad for collector 1 cm².

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



Ceramic PCB, Al₂O₃, standard footprint

Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

20 V, 8 A NPN low VCEsat transistor

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{(BR)CBO}	collector-base breakdown voltage	$I_C = 100 \ \mu A; I_E = 0 \ A; T_{amb} = 25 \ ^{\circ}C$	20	-	-	V
/ _{(BR)CEO}	collector-emitter breakdown voltage	$I_C = 10 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	20	-	-	V
/ _{(BR)EBO}	emitter-base breakdown voltage	$I_E = 100 \mu A; I_C = 0 A; T_{amb} = 25 °C$	5	-	-	V
СВО	collector-base cut-off	V _{CB} = 20 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	$V_{CB} = 20 \text{ V}; I_E = 0 \text{ A}; T_j = 150 ^{\circ}\text{C}$	-	-	50	μΑ
CES	collector-emitter cut-off current	V _{CE} = 16 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	100	nA
EBO	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
h _{FE}	DC current gain	V_{CE} = 2 V; I_{C} = 500 mA; pulsed; $t_{p} \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	300	620	-	
		V_{CE} = 2 V; I_{C} = 1 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	300	605	-	
		V_{CE} = 2 V; I_{C} = 2 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	300	590	-	
		V_{CE} = 2 V; I_{C} = 4 A; pulsed; $t_{p} \le 300 \ \mu s$; δ ≤ 0.02; T_{amb} = 25 °C	250	550	-	
		V_{CE} = 2 V; I_{C} = 8 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	250	480	-	
/ _{CEsat}	collector-emitter saturation voltage	I_C = 1 A; I_B = 10 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	30	40	mV
		I_C = 1 A; I_B = 50 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	20	30	mV
		I_C = 2 A; I_B = 40 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	40	55	mV
		I_C = 4 A; I_B = 40 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	75	105	mV
		I_C = 4 A; I_B = 200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	60	85	mV
		I_C = 8 A; I_B = 400 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	120	170	mV
R _{CEsat}	collector-emitter saturation resistance	I_C = 6 A; I_B = 600 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	14	20	mΩ
/ _{BEsat}	base-emitter saturation voltage	I_C = 1 A; I_B = 100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	0.83	0.9	V
		I_C = 4 A; I_B = 400 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	0.97	1.05	V
/ _{BE}	base-emitter voltage	V_{CE} = 2 V; I_{C} = 2 A; pulsed; $t_{p} \le 300 \mu s$; δ ≤ 0.02; T_{amb} = 25 °C	-	0.73	0.85	V

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t _d	delay time	V _{CC} = 12.5 V; I _C = 1 A; I _{Bon} = 0.05 A;	-	70	-	ns
t _r	rise time	I _{Boff} = -0.05 A; T _{amb} = 25 °C	-	40	-	ns
t _{on}	turn-on time		-	110	-	ns
t _s	storage time		-	545	-	ns
t _f	fall time		-	60	-	ns
t _{off}	turn-off time		-	605	-	ns
f _T	transition frequency	V_{CE} = 10 V; I_{C} = 100 mA; f = 100 MHz; T_{amb} = 25 °C	-	90	-	MHz
C _c	collector capacitance	V_{CB} = 10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C	-	116	-	pF

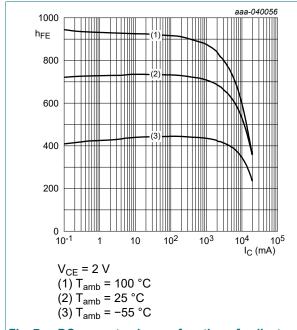


Fig. 7. DC current gain as a function of collector current; typical values

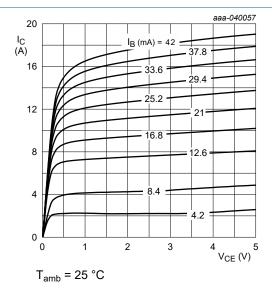


Fig. 8. Collector current as a function of collectoremitter voltage; typical values

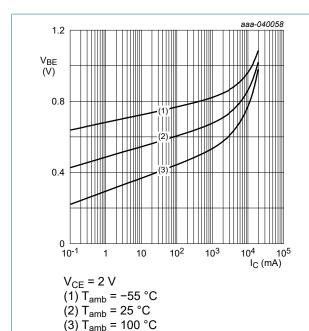


Fig. 9. Base-emitter voltage as a function of collector current; typical values

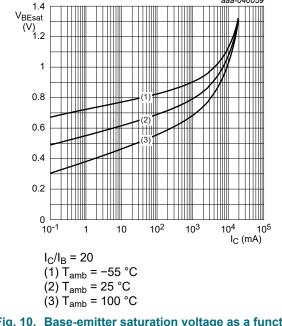


Fig. 10. Base-emitter saturation voltage as a function of collector current; typical values

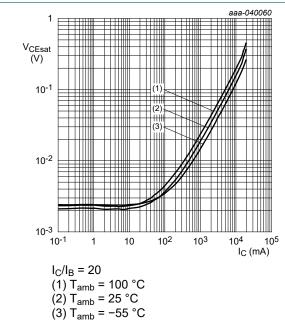
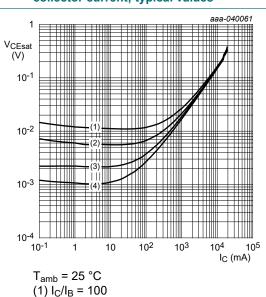
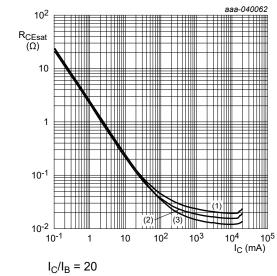


Fig. 11. Collector-emitter saturation voltage as a function of collector current; typical values



(1) $I_C/I_B = 100$ (2) $I_C/I_B = 50$ (3) $I_C/I_B = 20$ (4) $I_C/I_B = 10$

Fig. 12. Collector-emitter saturation voltage as a function of collector current; typical values



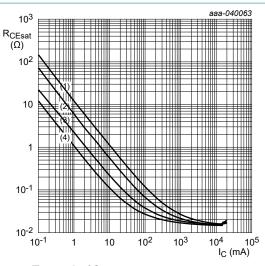
$$I_{C}/I_{B} = 20$$

(1)
$$T_{amb}$$
 = 100 °C

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 13. Collector-emitter saturation resistance as a function of collector current; typical values



$$(1) I_{\rm C}/I_{\rm B} = 100$$

(2)
$$I_C/I_B = 50$$

(3) $I_C/I_B = 20$

(3)
$$I_C/I_B = 20$$

(4) $I_C/I_B = 10$

Fig. 14. Collector-emitter saturation resistance as a

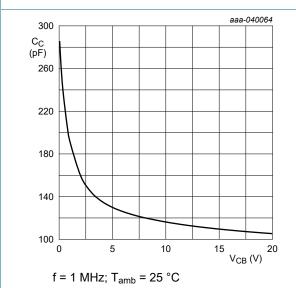
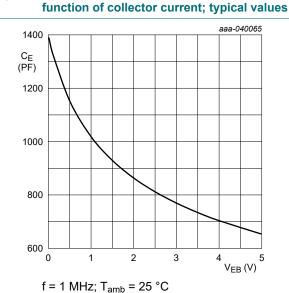


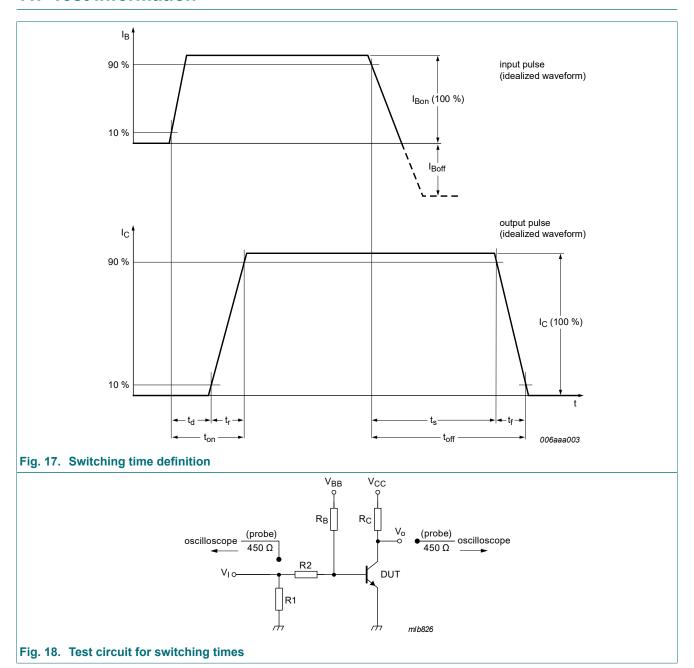
Fig. 15. Collector capacitance as a function of collector- Fig. 16. Emitter capacitance as a function of emitterbase voltage; typical values



base voltage; typical values

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11. Test information

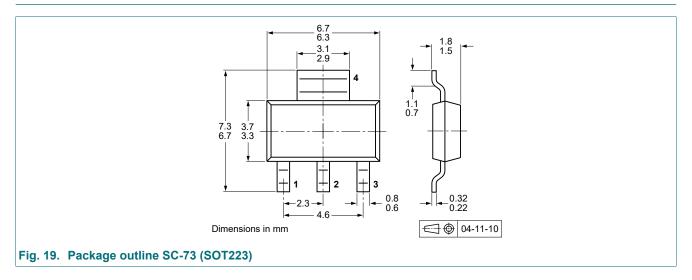


Quality information

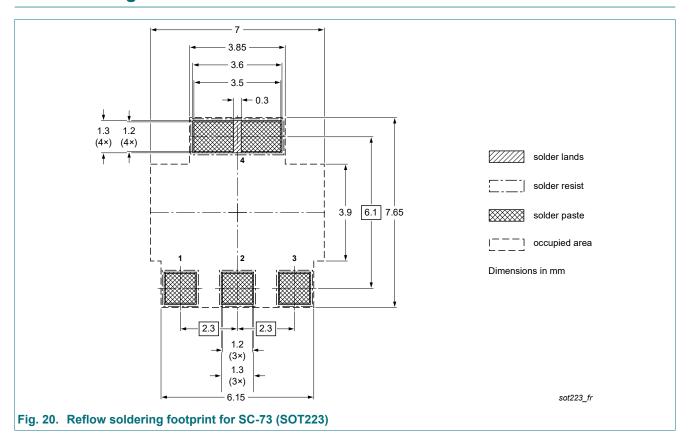
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

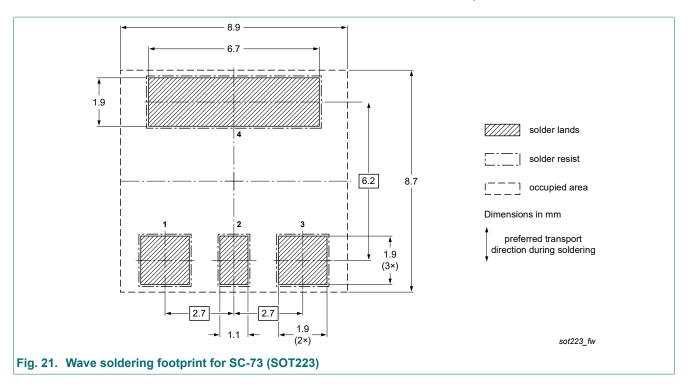
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12. Package outline



13. Soldering





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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PBSS4021NZ v.2	20240920	Product data sheet	-	PBSS4021NZ v.1		
Modifications:	New graphs added, graphs updated and values changed.Section "Packing information" removed.					
PBSS4021NZ v.1	20100331	Product data sheet	-	-		

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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